

MOSFET

600V CoolMOS™ CE Power Transistor

CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies. CoolMOS™ CE is a price-performance optimized platform enabling to target cost sensitive applications in Consumer and Lighting markets by still meeting highest efficiency standards. The new series provides all benefits of a fast switching Superjunction MOSFET while not sacrificing ease of use and offering the best cost down performance ratio available on the market.



Features

- Extremely low losses due to very low FOM $R_{DS(on)} \cdot Q_g$ and E_{oss}
- Very high commutation ruggedness
- Easy to use/drive
- Pb-free plating, Halogen free mold compound
- Qualified for standard grade applications

Applications

PFC stages, hard switching PWM stages and resonant switching stages for e.g. PC Silverbox, Adapter, LCD & PDP TV and indoor lighting.

Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

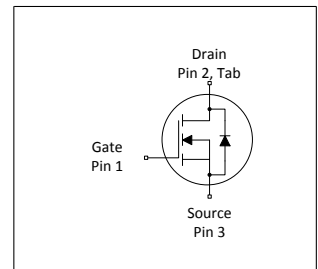


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	800	mΩ
I_d	8.4	A
$Q_{g,typ}$	17.2	nC
$I_{D,pulse}$	15.7	A
$E_{oss@400V}$	1.6	μJ

Type / Ordering Code	Package	Marking	Related Links
IPS60R800CE	PG-TO 251	60S800CE	see Appendix A

Table of Contents

Description	1
Maximum ratings	3
Thermal characteristics	3
Electrical characteristics	4
Electrical characteristics diagrams	6
Test Circuits	10
Package Outlines	11
Appendix A	12
Revision History	13
Trademarks	13
Disclaimer	13

1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	8.4 5.3	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	15.7	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	72	mJ	$I_D=1\text{A}$; $V_{DD}=50\text{V}$; see table 11
Avalanche energy, repetitive	E_{AR}	-	-	0.17	mJ	$I_D=1\text{A}$; $V_{DD}=50\text{V}$; see table 11
Avalanche current, repetitive	I_{AR}	-	-	1.0	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	50	V/ns	$V_{DS}=0\dots480\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC ($f>1\text{ Hz}$)
Power dissipation (Non FullPAK) TO-251	P_{tot}	-	-	74	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-40	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-40	-	150	$^\circ\text{C}$	-
Continuous diode forward current	I_S	-	-	5.9	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	15.7	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	15	V/ns	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 9
Maximum diode commutation speed	di/dt	-	-	500	A/ μs	$V_{DS}=0\dots400\text{V}$, $I_{SD}\leq I_S$, $T_j=25^\circ\text{C}$ see table 9

2 Thermal characteristics

Table 3 Thermal characteristics TO-251

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.70	$^\circ\text{C/W}$	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	$^\circ\text{C/W}$	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	35	45	$^\circ\text{C/W}$	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm ² (one layer, 70 μm thickness) copper area for drain connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature, wave & reflow soldering allowed	T_{sold}	-	-	260	$^\circ\text{C}$	reflow MSL1

¹⁾ Limited by $T_{j,max}$. Maximum duty cycle $D=0.50$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	$V_{GS}=0V, I_D=0.25mA$
Gate threshold voltage	$V_{(GS)th}$	2.5	3.0	3.5	V	$V_{DS}=V_{GS}, I_D=0.17mA$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=600, V_{GS}=0V, T_j=25^\circ C$ $V_{DS}=600, V_{GS}=0V, T_j=150^\circ C$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.68	0.80	Ω	$V_{GS}=10V, I_D=2A, T_j=25^\circ C$ $V_{GS}=10V, I_D=2A, T_j=150^\circ C$
Gate resistance	R_G	-	11	-	Ω	$f=1MHz, \text{open drain}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	373	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
Output capacitance	C_{oss}	-	27	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1MHz$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	18	-	pF	$V_{GS}=0V, V_{DS}=0...480V$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	74	-	pF	$I_D=\text{constant}, V_{GS}=0V, V_{DS}=0...480V$
Turn-on delay time	$t_{d(on)}$	-	9	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.5A,$ $R_G=6.8\Omega; \text{see table 10}$
Rise time	t_r	-	7	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.5A,$ $R_G=6.8\Omega; \text{see table 10}$
Turn-off delay time	$t_{d(off)}$	-	50	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.5A,$ $R_G=6.8\Omega; \text{see table 10}$
Fall time	t_f	-	12	-	ns	$V_{DD}=400V, V_{GS}=13V, I_D=2.5A,$ $R_G=6.8\Omega; \text{see table 10}$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{GS}	-	2	-	nC	$V_{DD}=480V, I_D=2.5A, V_{GS}=0 \text{ to } 10V$
Gate to drain charge	Q_{gd}	-	8.9	-	nC	$V_{DD}=480V, I_D=2.5A, V_{GS}=0 \text{ to } 10V$
Gate charge total	Q_g	-	17.2	-	nC	$V_{DD}=480V, I_D=2.5A, V_{GS}=0 \text{ to } 10V$
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	$V_{DD}=480V, I_D=2.5A, V_{GS}=0 \text{ to } 10V$

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{o(BR)DSS}$

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{o(BR)DSS}$

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V, I_F=2.5A, T_j=25^\circ C$
Reverse recovery time	t_{rr}	-	250	-	ns	$V_R=400V, I_F=2.5A, di_F/dt=100A/\mu s$; see table 9
Reverse recovery charge	Q_{rr}	-	1.8	-	μC	$V_R=400V, I_F=2.5A, di_F/dt=100A/\mu s$; see table 9
Peak reverse recovery current	I_{rrm}	-	16	-	A	$V_R=400V, I_F=2.5A, di_F/dt=100A/\mu s$; see table 9

4 Electrical characteristics diagrams

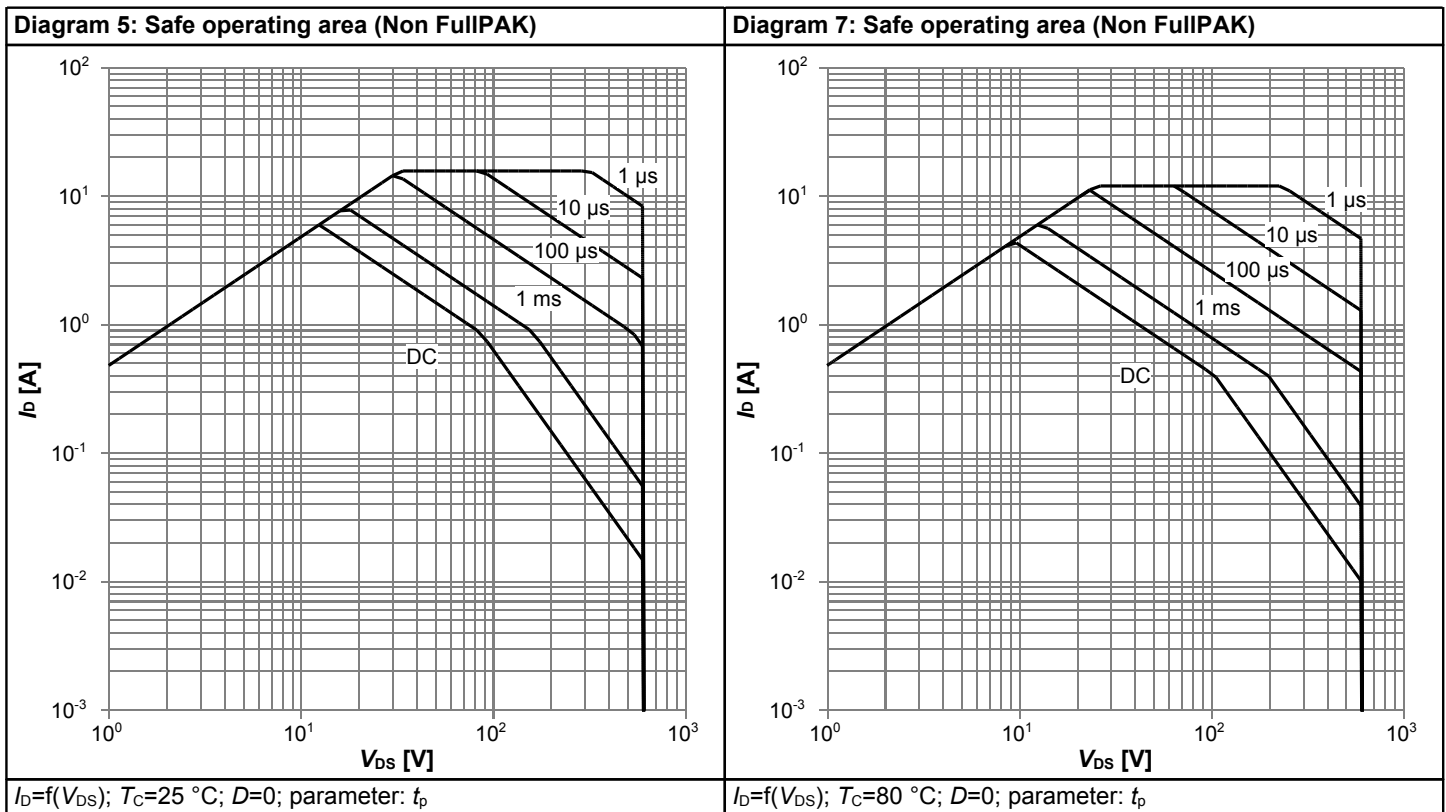
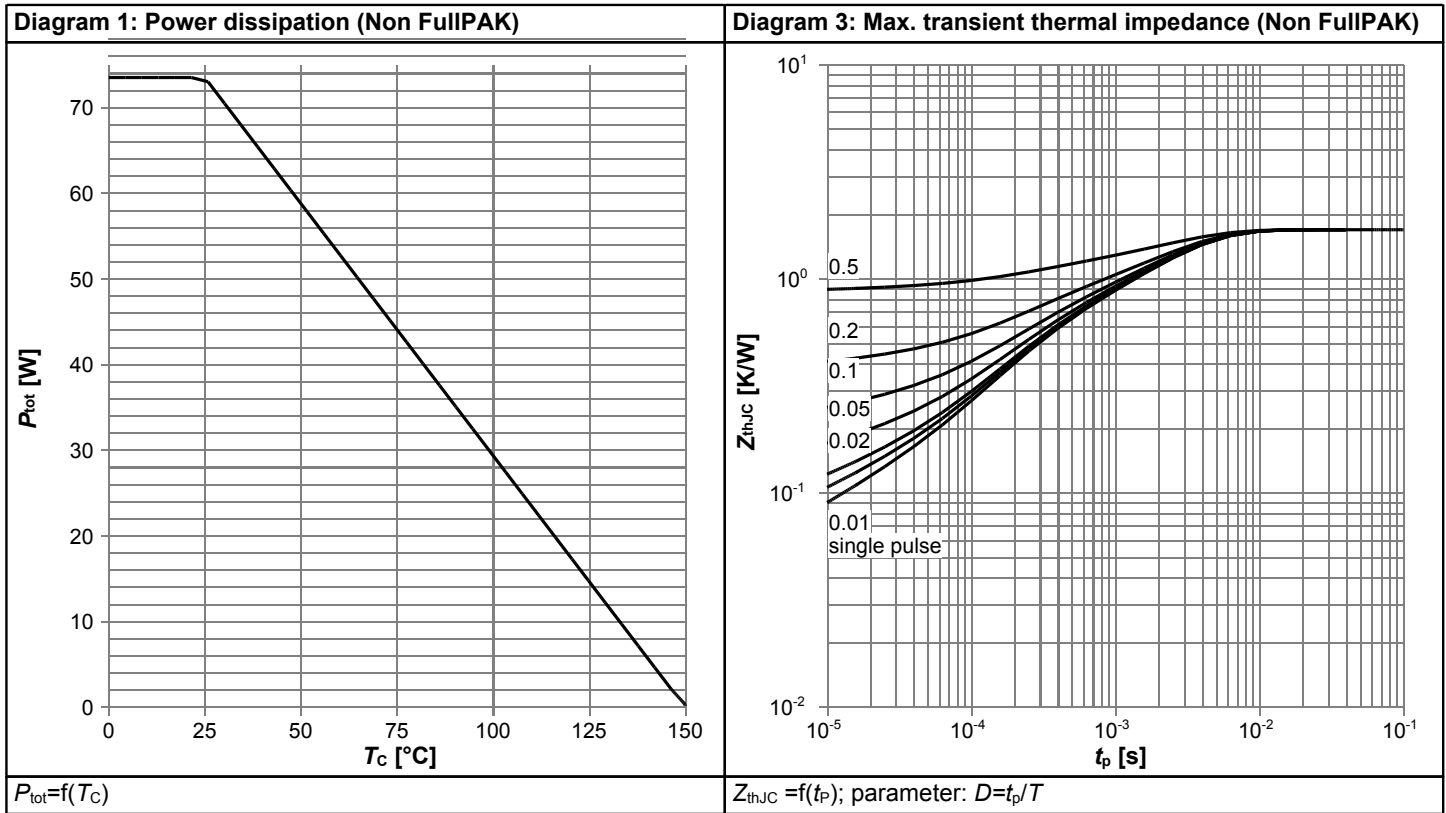
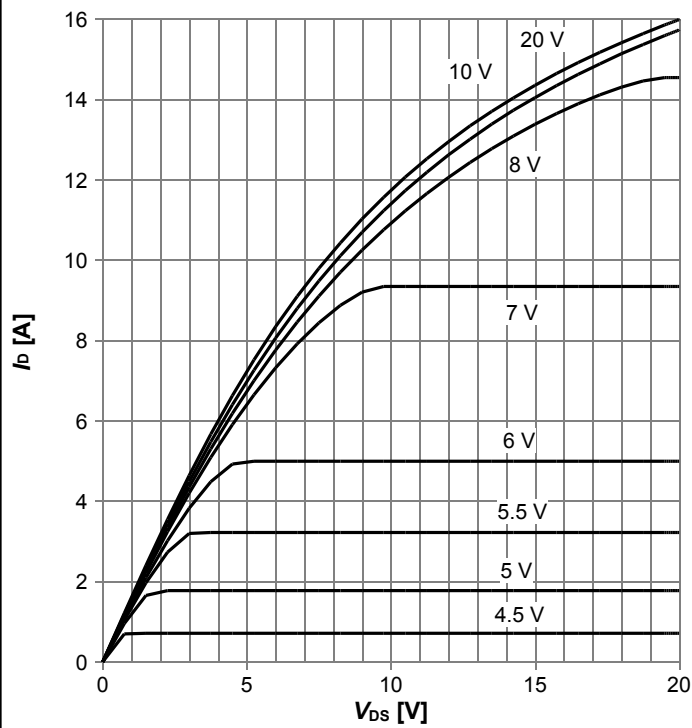
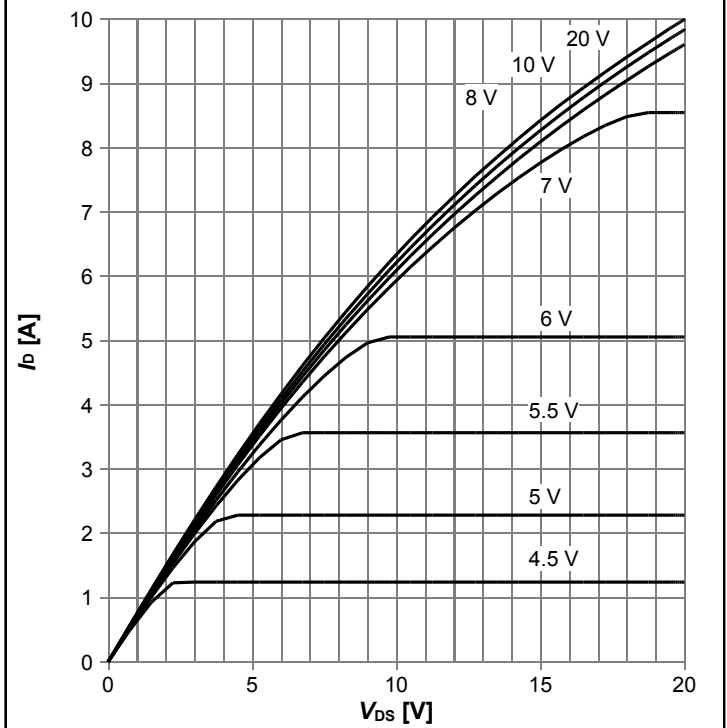


Diagram 9: Typ. output characteristics



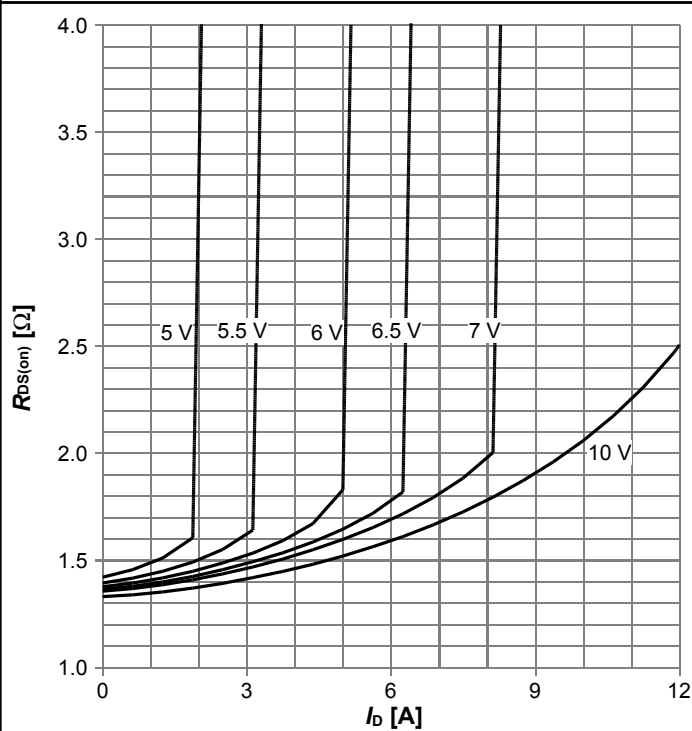
$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 10: Typ. output characteristics



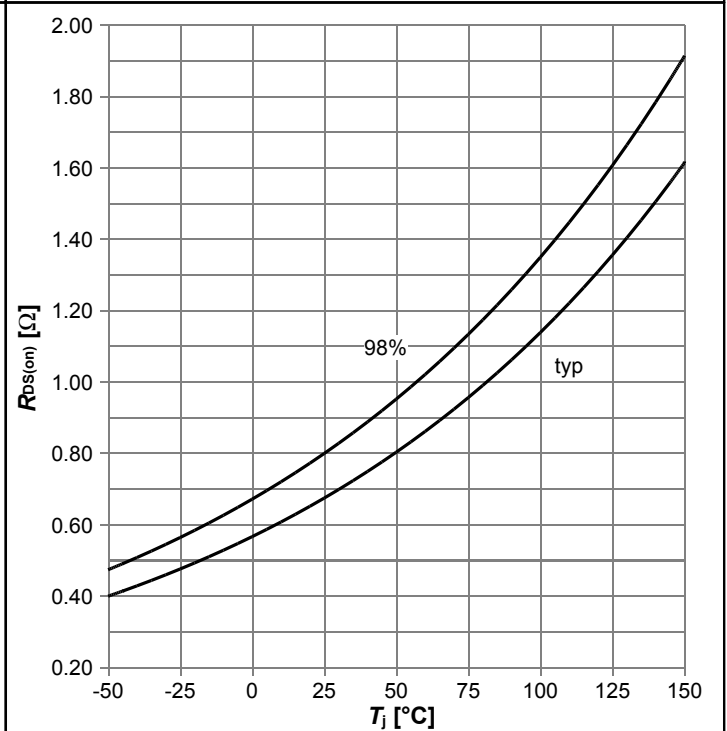
$I_D = f(V_{DS})$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Diagram 11: Typ. drain-source on-state resistance



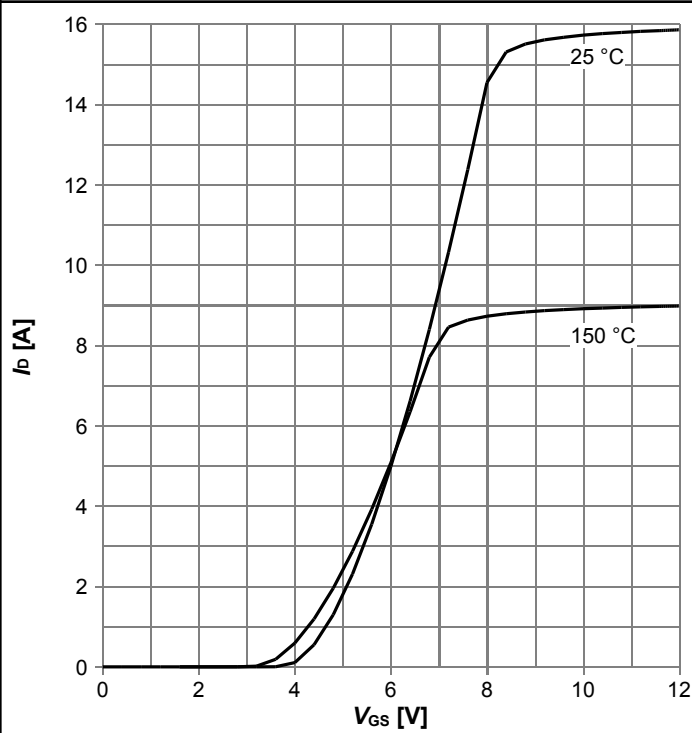
$R_{DS(on)} = f(I_D)$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Diagram 12: Drain-source on-state resistance



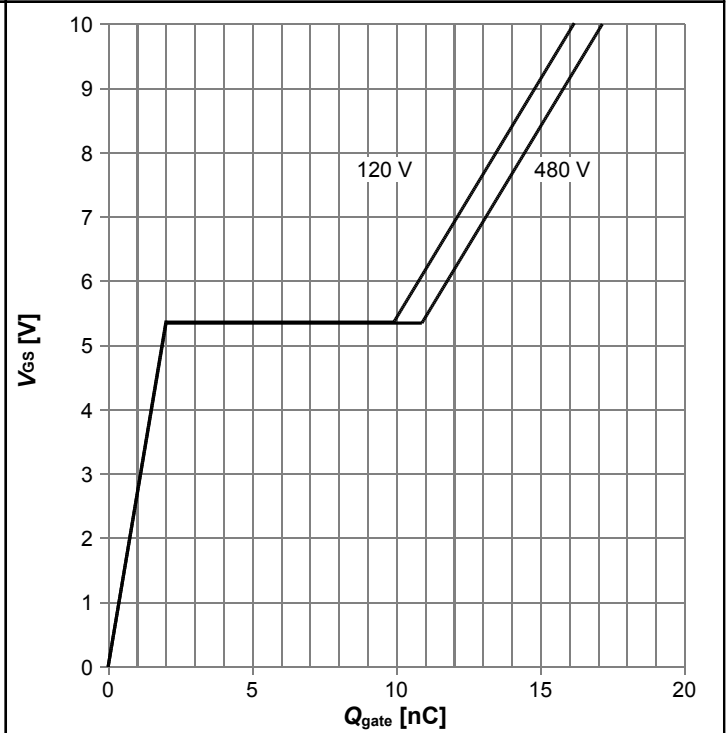
$R_{DS(on)} = f(T_j)$; $I_D = 2.0\text{ A}$; $V_{GS} = 10\text{ V}$

Diagram 13: Typ. transfer characteristics



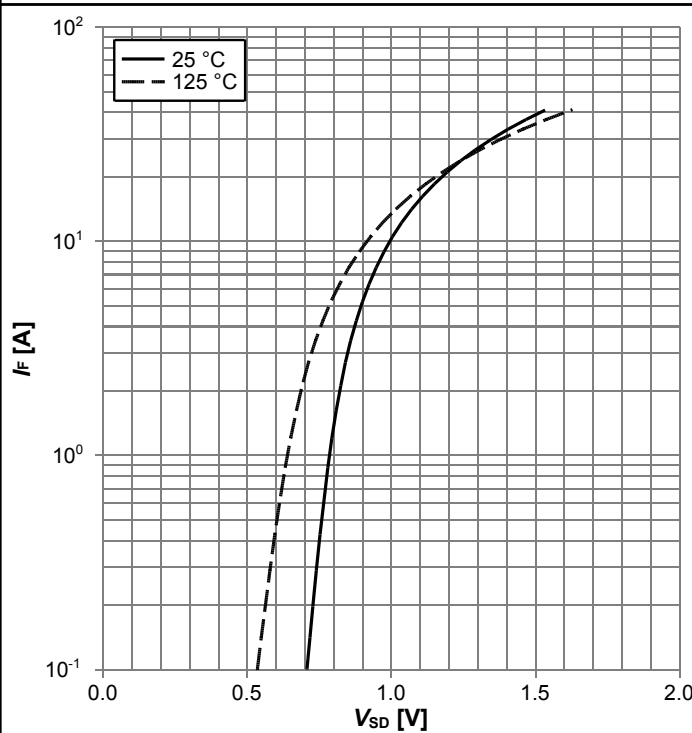
$I_D = f(V_{GS})$; $V_{DS} = 20V$; parameter: T_j

Diagram 14: Typ. gate charge



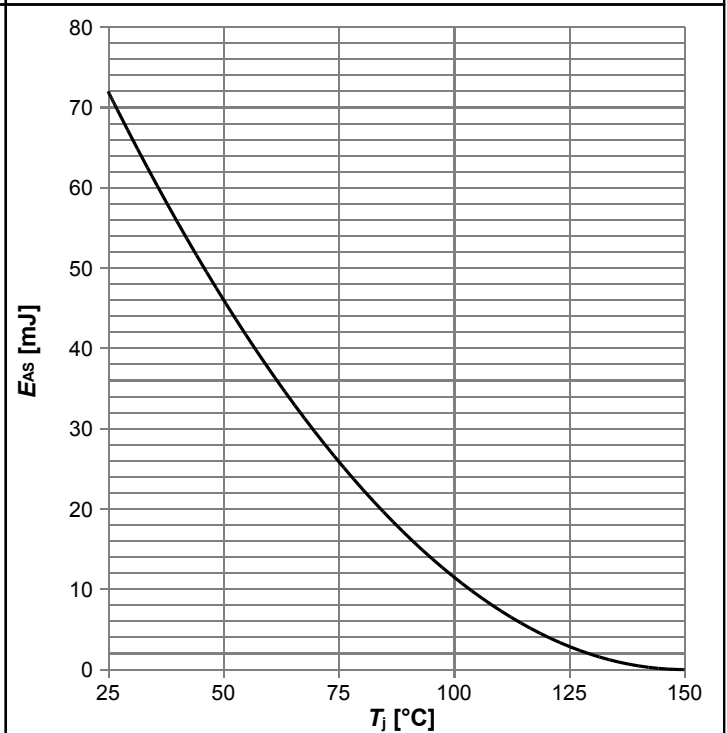
$V_{GS} = f(Q_{gate})$; $I_D = 2.5 A$ pulsed; parameter: V_{DD}

Diagram 15: Forward characteristics of reverse diode



$I_F = f(V_{SD})$; parameter: T_j

Diagram 16: Avalanche energy

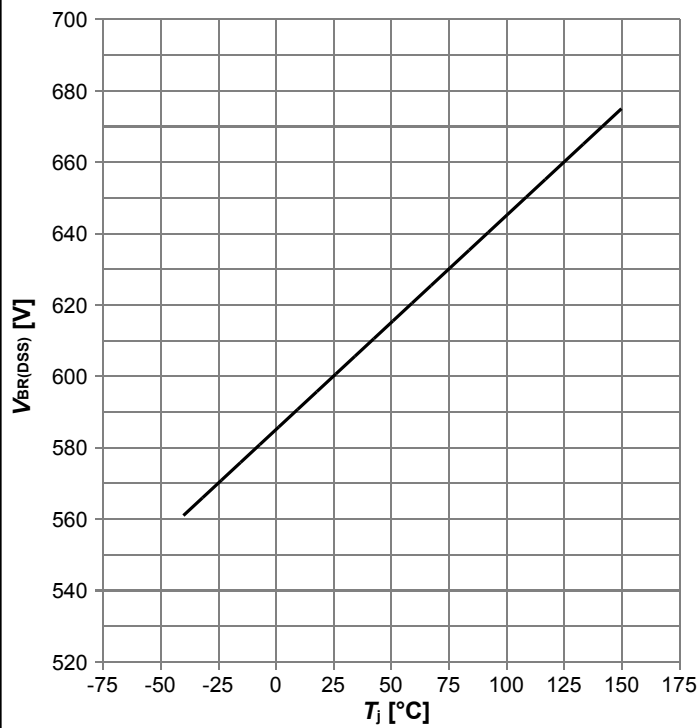


$E_{AS} = f(T_j)$; $I_D = 1.0 A$; $V_{DD} = 50 V$

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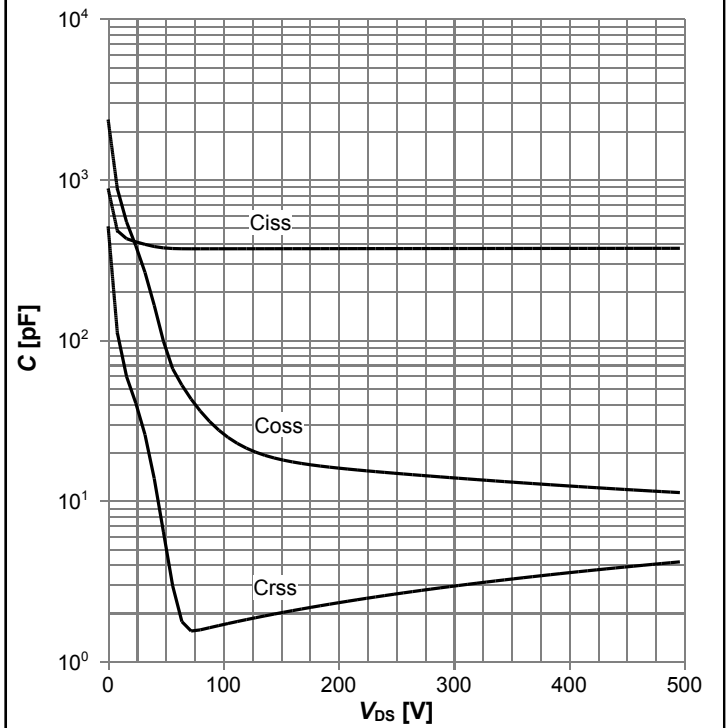
IPS60R800CE

Diagram 17: Drain-source breakdown voltage



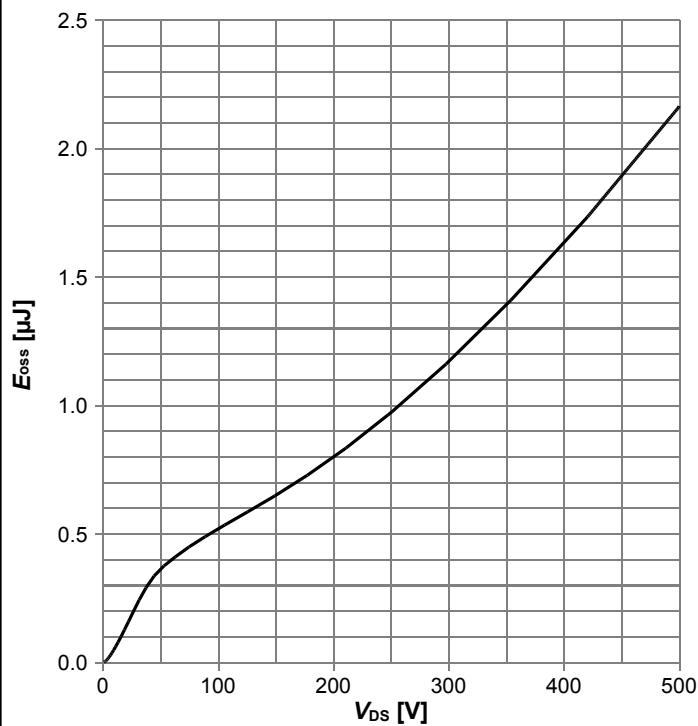
$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$

Diagram 18: Typ. capacitances



$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

Diagram 19: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test Circuits

Table 8 Diode characteristics

Test circuit for diode characteristics	Diode recovery waveform
<p>$R_{g1} = R_{g2}$</p>	<p>$t_{rr} = t_F + t_S$ $Q_{rr} = Q_F + Q_S$</p>

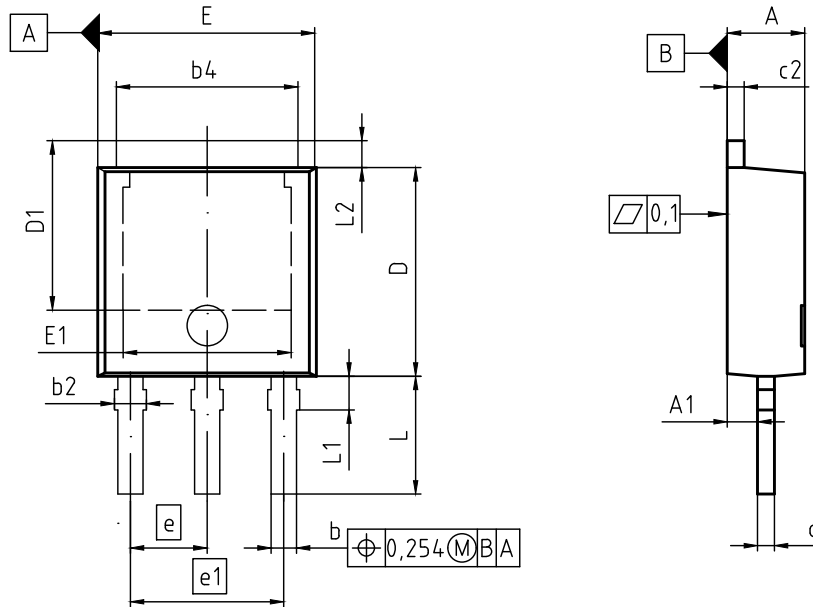
Table 9 Switching times

Switching times test circuit for inductive load	Switching times waveform

Table 10 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform
	<p>$V_{(BR)DS}$</p>

6 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.18	2.40	0.086	0.094
A1	0.80	1.14	0.031	0.045
b	0.64	0.89	0.025	0.035
b2	0.65	1.15	0.026	0.045
b4	4.95	5.50	0.195	0.217
c	0.46	0.59	0.018	0.023
c2	0.46	0.89	0.018	0.035
D	5.97	6.22	0.235	0.245
D1	5.04	5.55	0.198	0.219
E	6.35	6.73	0.250	0.265
E1	4.60	5.21	0.181	0.205
e	2.29		0.090	
e1	4.57		0.180	
N	3		3	
L	3.00	3.60	0.118	0.142
L1	0.80	1.25	0.031	0.049
L2	0.88	1.28	0.035	0.050

DOCUMENT NO. Z8B00003329
SCALE
EUROPEAN PROJECTION
ISSUE DATE 21-10-2015
REVISION 06

Figure 1 Outline PG-TO 251, dimensions in mm/inches

7 Appendix A

Table 11 Related Links

- IFX CoolMOS™ CE Webpage: www.infineon.com
- IFX CoolMOS™ CE application note: www.infineon.com
- IFX CoolMOS™ CE simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

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IPS60R800CE

Revision History

IPS60R800CE

Revision: 2016-02-26, Rev. 2.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2016-02-26	Release of final version

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Published by

Infineon Technologies AG

81726 München, Germany

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